

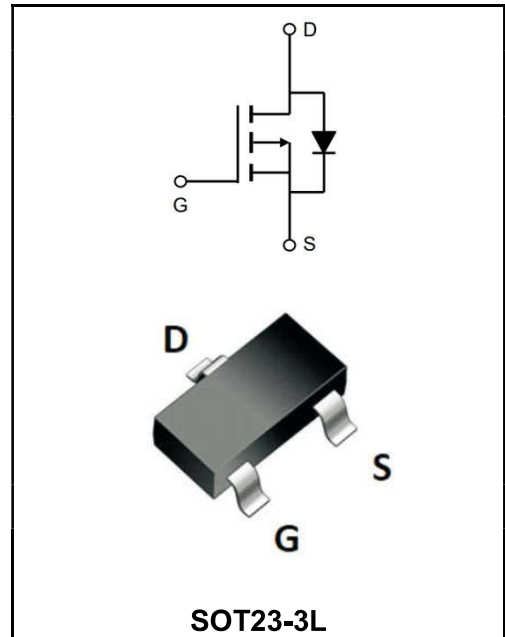
-60V P-CHANNEL ENHANCEMENT MODE MOSFET

MAIN CHARACTERISTICS

I_D	-3.8A
V_{DSS}	-60V
R_{DS(on)-typ(@V_{GS}=-10V)}	< -150mΩ(Type:125 mΩ)

Application

- ◆Battery protection
- ◆Load switch
- ◆Uninterruptible power supply



Product Specification Classification

Part Number	Package	Marking	Pack
YFW3P06MI	SOT23-3L	W3P6	3000PCS/Tape

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	-60	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current, V _{GS} @ -10V ¹ @T _A =25°C	I_D	-3.8	A
Continuous Drain Current, V _{GS} @ -10V ¹ @T _A =70°C	I_D	-2.4	A
Pulsed Drain Current ²	I_{DM}	-12	A
Total Power Dissipation ³ @T _A =25°C	P_D	1.5	W
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C
Thermal Resistance Junction-Ambient ¹	R_{θJA}	125	°C/W
Thermal Resistance Junction-Case ¹	R_{θJC}	80	°C/W

Maximum Ratings at Tc=25°C unless otherwise specified

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	BV_{DSS}	-60	-67	-	V
BVDSS Temperature Coefficient	Reference to 25°C, $I_D=-1mA$	$\Delta BV_{DSS}/\Delta T_J$	-	-0.021	-	V/°C
Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-1.5A$	$R_{DS(ON)}$	-	125	150	mΩ
	$V_{GS}=-4.5V, I_D=-1A$		-	158	200	
Gate -Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	$V_{GS(th)}$	-1.0	1.7	-2.5	V
$V_{GS(th)}$ Temperature Coefficient		$\Delta V_{GS(th)}$	-	4.08	-	mV/°C
Drain -Source Leakage Current	$V_{DS}=-48V, V_{GS}=0V, T_J=25^\circ C$	I_{DSS}	-	-	1	μA
	$V_{DS}=-48V, V_{GS}=0V, T_J=55^\circ C$		-	-	5	
Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	I_{GSS}	-	-	±100	nA
Forward Transconductance	$V_{DS}=-5V, I_D=-1.5A$	g_{FS}	-	5.9	-	S
Total Gate Charge(-4.5V)	$V_{DS}=-20V$ $V_{GS}=-4.5V$ $I_D=-1.5A$	Q_g	-	4.6	-	nC
Gate-Source Charge		Q_{gs}	-	1.4	-	
Gate-Drain Charge		Q_{gd}	-	1.62	-	
Turn-on delay time	$V_{DS}=-15V$ $V_{GS}=-10V$ $R_G=3.3\Omega$ $I_D=-1A$	$t_{d(on)}$	-	17.4	-	nS
Rise Time		T_r	-	5.4	-	
Turn-Off Delay Time		$t_{d(OFF)}$	-	37.2	-	
Fall Time		t_f	-	2.4	-	
Input Capacitance	$V_{DS}=-15V$ $V_{GS}=0V$ $f=1.0MHz$	C_{iss}	-	531	-	pF
Output Capacitance		C_{oss}	-	59	-	
Reverse Transfer Capacitance		C_{rss}	-	38	-	
Continuous Source Current ^{1,4}	$V_G=V_D=0V, \text{ Force Current}$	I_S	-	-	-1.7	A
Pulsed Source Current ^{2,4}		I_{SM}	-	-	-7	A
Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ C$	V_{SD}	-	-	-1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\cong 300\mu s$, duty cycle $\cong 2\%$
- 3、The power dissipation is limited by 150°C junction temperature
- 4、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Ratings and Characteristic Curves

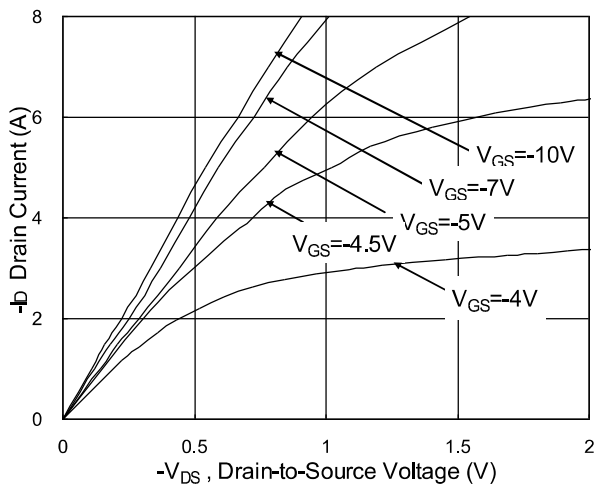


Fig.1 Typical Output Characteristics

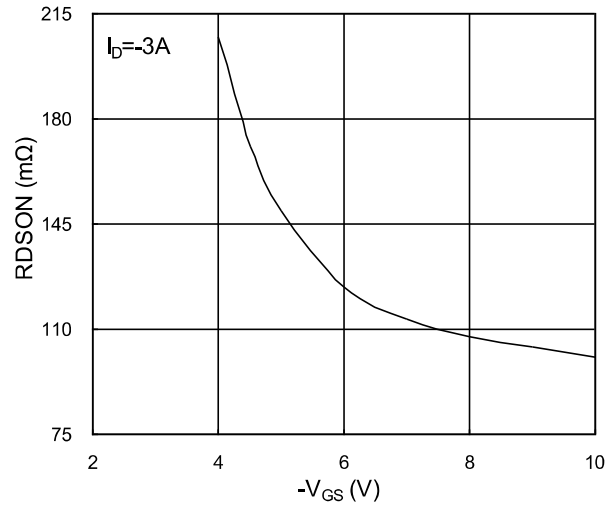


Fig.2 On-Resistance vs. G-S Voltage

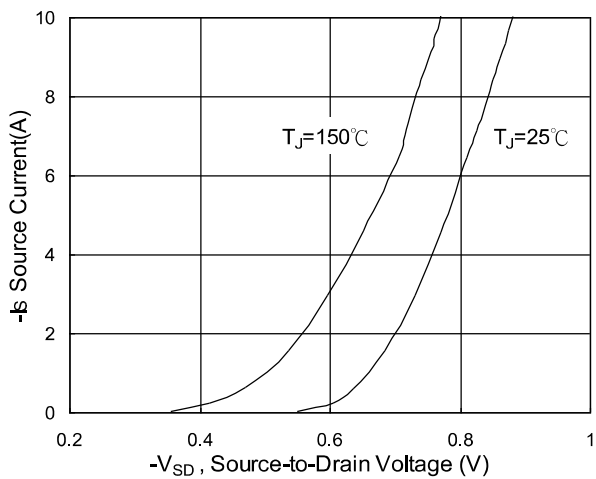


Fig.3 Forward Characteristics Of Reverse

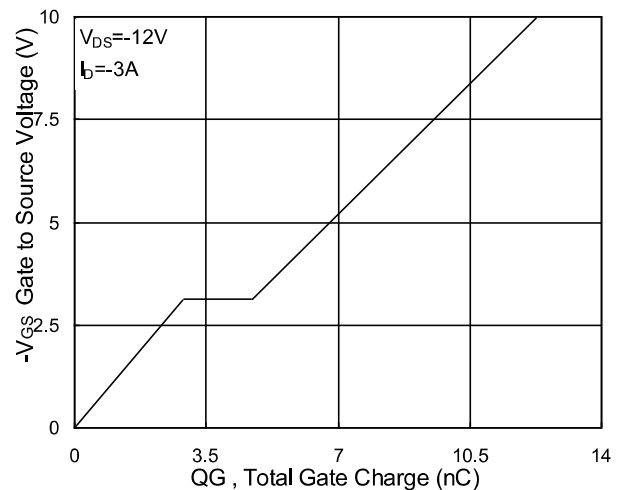


Fig.4 Gate-Charge Characteristics

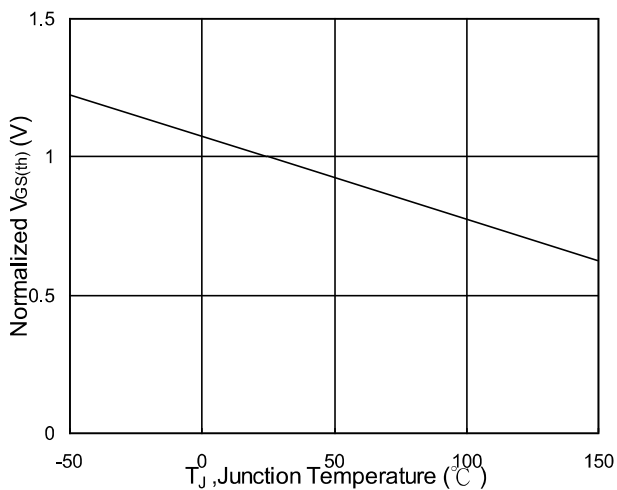


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

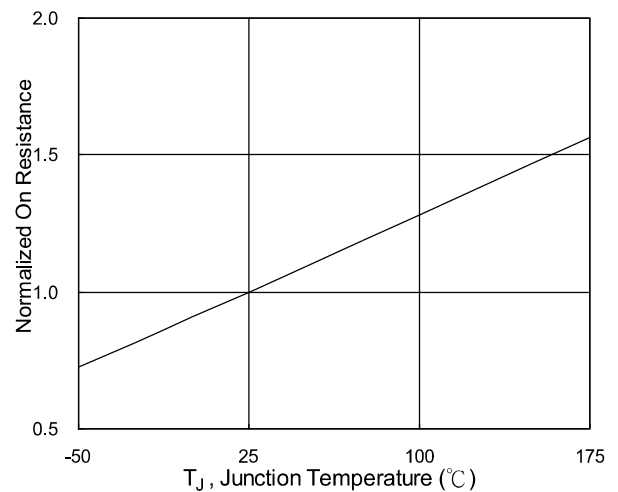


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

Ratings and Characteristic Curves

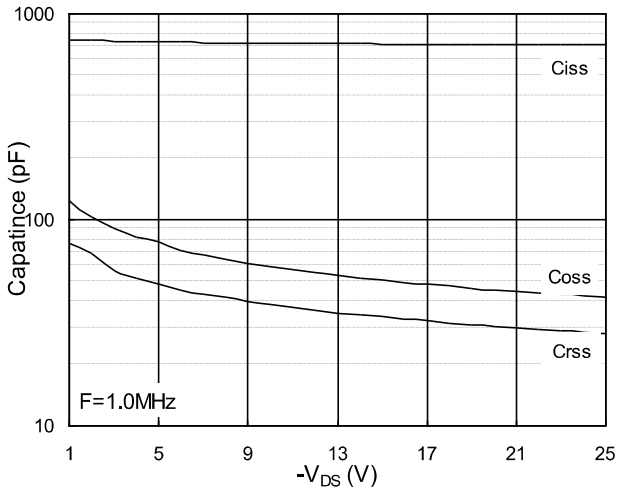


Fig.7 Capacitance

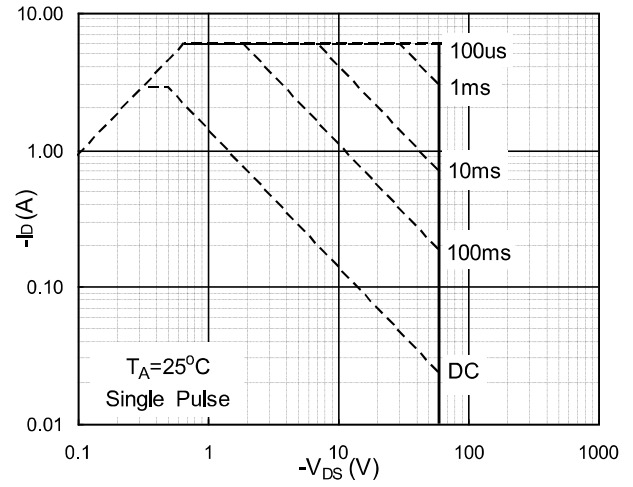


Fig.8 Safe Operating Area

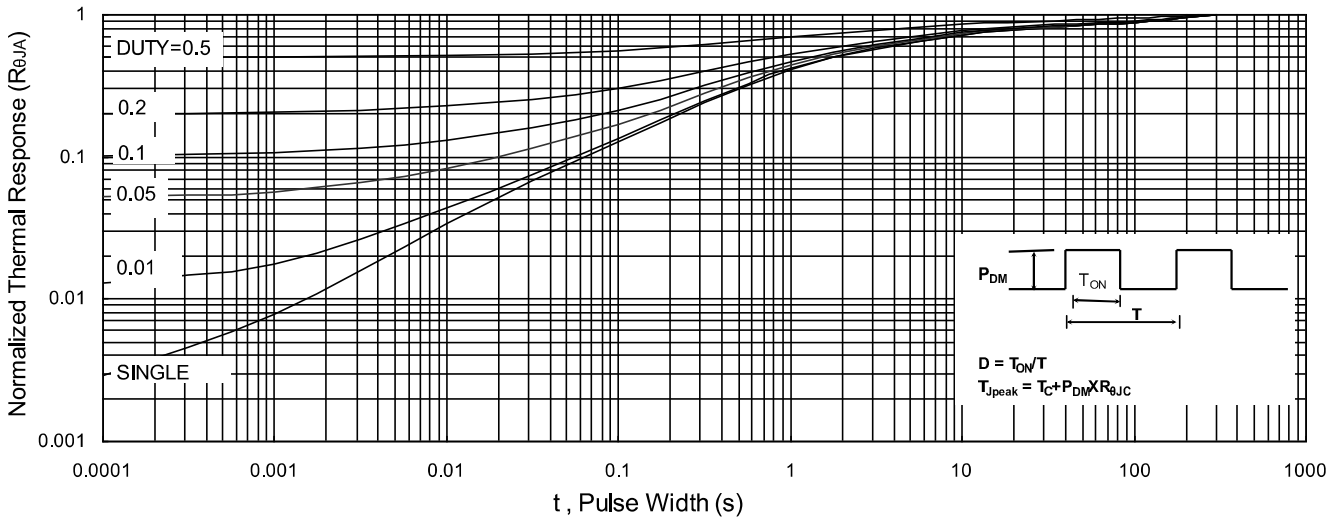


Fig.9 Normalized Maximum Transient Thermal Impedance

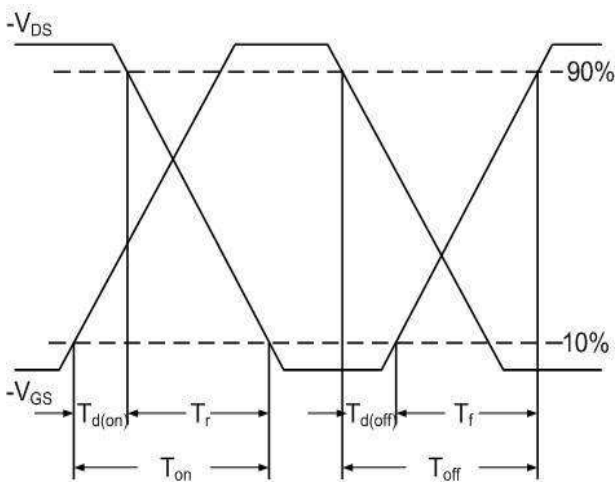


Fig.10 Switching Time Waveform

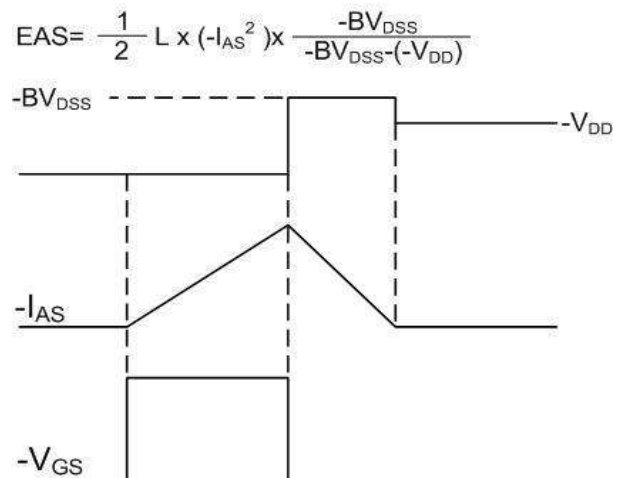
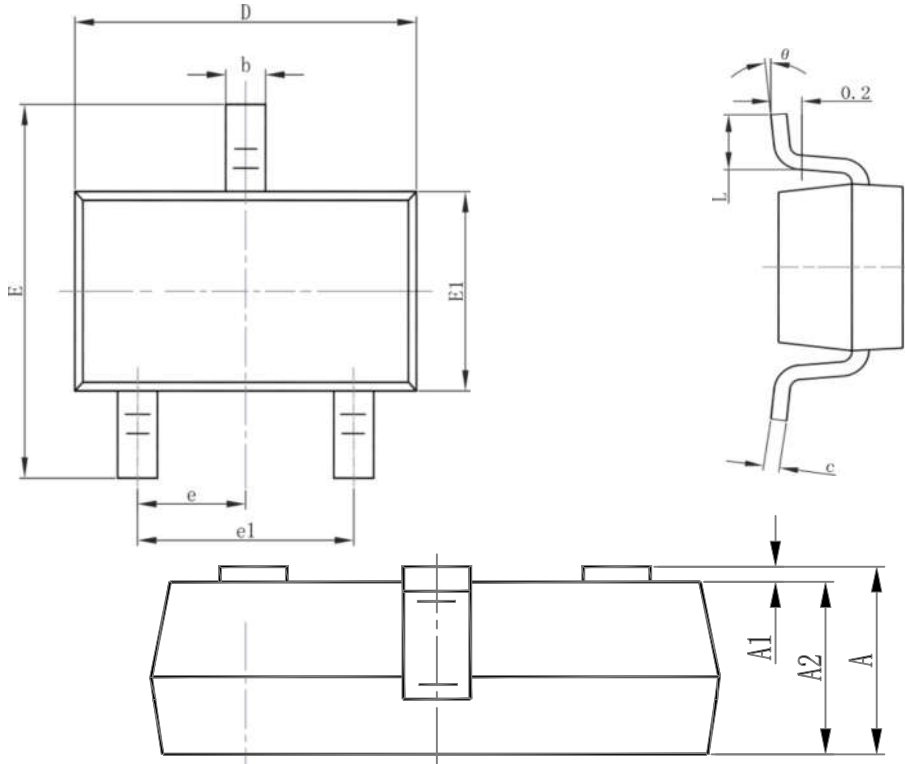


Fig.11 Unclamped Inductive Waveform

SOT23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°